

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of:
Kwang N. Kim, et al.

Application No.: TBD

Group Art Unit: TBD

Filed: TBD

Examiner: TBD

For: **METHOD OF FORMING SILICON OXIDE
LAYER AND METHOD OF
MANUFACTURING THIN FILM
TRANSISTOR THEREBY**

FIRST PRELIMINARY AMENDMENT

MS Patent Application
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Dear Sir:

INTRODUCTORY COMMENTS

Prior to examination on the merits, please amend the above-identified U.S. patent application as follows:

Amendments to the Specification are reflected in the listing of claims which begins on page 2 of this paper.

Remarks/Arguments begin on page 3 of this paper.